

EAST Search History (15 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 14:19
S1	4	"264914".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/20 09:44
S2	6	"760087".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S3	3	("6808971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S4	1	"6429085".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:27
S5	1	"5006913".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:42
S6	1	"4768076".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:43
S7	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:44
S8	8	((("4692994") or ("4768076") or ("5006913") or ("6429085"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 07:44
S9	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2005/09/07 07:45
S10	0	battacharyya.in. and strained and (sige gesi si-ge ge-si silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S11	0	battacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S12	644	bhattacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57

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S13	73	bhattacharyya.in. and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S14	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:57
S15	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:58
S16	35	bhattacharyya.in. and cmos and (thin adj film TFT) and strained. clm. and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:17
S17	11	(inverter invertor).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:24
S18	11	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S19	34	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge. sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26

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S20	5	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti, ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and @ad<"20020311"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 10:33
S21	2	("5298452").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:46
S22	191	speed near4 CMOS near4 (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:47
S23	1	improve near4 speed near4 CMOS near4 (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:49
S24	44	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 11:06
S25	49	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:09
S26	14	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter invertor) and (single adj crystal monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:08
S27	23	"6251751"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:41
S28	18	S27 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42

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S29	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S30	1	S29 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:19
S31	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S32	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S33	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:25
S34	28	polycrystalline near4 silicon adj germanium near10 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:26
S35	8	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S36	1	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S37	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S38	2	silicon adj germanium near4 band adj gap near4 wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05

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S39	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:12
S40	37	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:14
S41	10	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:20
S42	4900	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/07 16:20
S43	139	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S44	16	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4"Ge.sub."\$4 "Ge.sub."\$4"Si.sub."\$4) and (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S45	4	(("6251751") or ("5298452")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 21:18
S46	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:05
S47	1418	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:06
S48	1480	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:06

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S49	363	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S50	44	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and (silicon si) near3 (ge germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S51	57	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:08
S52	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:09
S53	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:10
S54	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:12
S55	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and (((silicon si) near3 (ge germanium)) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:19
S56	107	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet) and (inverter invertor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S57	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:23

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S58	1	"3793721".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S59	1	"4467518".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S60	1	"4489478".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S61	1	"4498226".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:25
S62	1	"4502202".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S63	1	"4555843".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S64	1	"4603468".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S65	1	"4649627".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S66	179	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S67	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 08:25
S68	0	S67 and composition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S69	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S70	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S71	252	graded near2 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S72	0	graded near2 contact and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26

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S73	0	(grade grading graded) near2 (contact via) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S74	5	(grade grading graded) near2 (contact via interconnect interconnection interconnexion) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S75	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 10:51
S76	0	(US-20040145399-\$).did. and (composition composed grade graded grading)	US-PGPUB	OR	ON	2006/01/29 10:52
S77	1	(US-20040145399-\$).did. and (composition composed grade graded grading doping concentration)	US-PGPUB	OR	ON	2006/01/29 11:31
S78	4	cmos adj inverter near6 computer. ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S79	4	cmos adj inverter near20. computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S80	22	cmos adj inverter.ti,ab,clm. and computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:33
S81	0	cmos adj inverter near10 (logic adj circuit).ti,ab,clm. and computer near10 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:34
S82	0	cmos adj inverter near20 (logic adj circuit).ti,ab,clm. and computer near20 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:35
S83	10	cmos adj inverter near3 computer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:37
S84	7	cmos adj inverter near6 computer not bhattacharyya.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:42
S85	2	("5774008").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 12:10

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S86	13	strained near10 relaxed near10 lattice and CMOS near1 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 13:27
S87	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
S88	6622	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
S89	2	S88 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:59
S90	2	S88 and (sige silicon adj germanium).ti,ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 14:00
S91	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 14:01
S92	2	("6649980").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:18
S93	5	"454304".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:24
S94	2	"6888750".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:25

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S95	2	("20030030091").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 18:27
S96	38	(single adj crystal monocrystalline) near6 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28
S97	36	(single adj crystal monocrystalline) near3 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28
S98	3	"6800892".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 12:10
S99	6	((("20040179391") or ("20040155317") or ("20040178826")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 14:33
S10 0	4	stacked adj (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:38
S10 1	68	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:41
S10 2	10	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and relaxed near6 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:42
S10 3	3	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and (CTE thermal adj expansion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:46
S10 4	453	(stacking stack stacked) near2 (TFT thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:46

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S10 5	101	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:50
S10 6	23110861	(stacking stack stacked) near2 (TFT thin adj film adj transistor)". ti,ab,clm.and" @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:51
S10 7	53	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti, ab,clm. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 14:54
S10 8	4	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti, ab,clm. and @ad<"20021004" and (SiGe si-ge silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 16:14
S11 1	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 18:24
S11 2	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:24
S11 3	1428	strained and relaxed and (silicon adj germanium sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:25
S11 4	1085	strained and relaxed and (silicon adj germanium sige silicon-germanium) and "257"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:25
S11 5	64	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:26

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S11 6	9	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:29
S11 7	9	strained and relaxed and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:30
S11 8	13	strained and relaxed and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:31
S11 9	611	first adj semiconductor adj (film layer) and second adj semiconductor adj (film layer) and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 18:32
S12 0	0	underfilm near10 (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 08:11
S12 1	2	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 08:12
S12 2	0	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon) and (tft thin adj film adj transistor "SOI")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:17
S12 3	1585	nickel and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:18
S12 4	541	nickel near10 catalyst and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:18

EAST Search History

S12 5	0	nickel near10 catalyst near10 (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:18
S12 6	2	nickel near10 catalyst with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:19
S12 7	48	nickel with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:25
S12 8	918	cmos adj inverter.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:25
S12 9	45	cmos adj inverter.ti. and "257"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:25
S13 0	16	cmos adj inverter.ti. and "327"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:26
S13 1	6	cmos adj inverter.ti. and "365"/\$7. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:26
S13 2	44	cmos adj inverter.ti.	USPAT	OR	ON	2006/11/02 10:28
S13 3	7740	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:29
S13 4	3	S133 and (silicon-germanium silicon near1 germanium sige) and (invert?r near1 CMOS) and (composition compositional compositionally) and stack\$3 near1 (transistor tft mosfet mos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:33

EAST Search History

S13 5	58	bhattacharyya.in. and tft and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:38
S13 6	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2). clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and nfet.clm. and pfet.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:42
S13 7	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2). clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft nfet).clm. and (tft pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:43
S13 8	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2). clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet).clm. and (tft thin adj film adj transistor pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:43
S13 9	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2). clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 10:48

EAST Search History

S14 0	40	(("4333808") or ("4488262") or ("4648179") or ("4870470") or ("4776922") or ("5811870") or ("5874778") or ("6344373") or ("7012297") or ("6700771") or ("6933572") or ("6743681") or ("6784480") or ("7132348") or ("6943065") or ("6828632") or ("6903001") or ("6917078") or ("6903969") or ("7042027") or ("6759712") or ("6873015") or ("6998683") or ("6882010") or ("6768156") or ("6800892") or ("6812504") or ("7042052") or ("6713810") or ("7026690") or ("6998667") or ("6845034") or ("6900667") or ("6888200") or ("6908798") or ("6873018") or ("6955960") or ("6982457") or ("7130216") or ("7019378") or ("6950340")).PN.	USPAT; JPO	OR	OFF	2006/11/02 11:20
S14 1	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 14:19
S14 2	1	("20030030091").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/11/02 11:20

inventor name search

Day : Thursday
Date: 11/2/2006
Time: 10:47:48

PALM INTRANET

Inventor Name Search Result

Your Search was:

Last Name = BHATTACHARYYA

First Name = ARUP

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>06089710</u>	Not Issued	161	10/30/1979	ULTRA-THIN FILM CAPACITOR AND METHOD FOR MANUFACTURE THEREOF	BHATTACHARYYA, ARUP
<u>06234084</u>	4333808	250	02/13/1981	METHOD FOR MANUFACTURE OF ULTRA-THIN FILM CAPACITOR	BHATTACHARYYA, ARUP
<u>06389204</u>	4488262	150	06/17/1982	ELECTRONICALLY PROGRAMMABLE READ ONLY MEMORY	BHATTACHARYYA, ARUP
<u>06509513</u>	4648179	150	06/30/1983	INTERCONNECTION STRUCTURE FOR SEMICONDUCTOR DEVICE	BHATTACHARYYA, ARUP
<u>07108886</u>	4870470	150	10/16/1987	NON-VOLATILE MEMORY CELL HAVING SI-RICH SILICON NITRIDE CHARGE TRAPPING LAYER	BHATTACHARYYA, ARUP
<u>07114959</u>	4776922	150	10/30/1987	FORMATION OF VARIABLE-WIDTH SIDEWALL STRUCTURES	BHATTACHARYYA, ARUP
<u>08850033</u>	5811870	150	05/02/1997	ANTIFUSE STRUCTURE	BHATTACHARYYA, ARUP
<u>08873102</u>	5874778	150	06/11/1997	EMBEDDED POWER AND GROUND PLANE STRUCTURE	BHATTACHARYYA, ARUP
<u>09079608</u>	Not Issued AB.	161	05/15/1998	METHOD FOR MAKING EMBEDDED POWER AND GROUND PLANE STRUCTURE	BHATTACHARYYA, ARUP
<u>09106980</u>	6344373	150	06/29/1998	A METHOD FOR FORMING AN ANTIFUSE	BHATTACHARYYA, ARUP
<u>09944985</u>	7012297	150	08/30/2001	SCALABLE FLASH/NV STRUCTURES AND DEVICES WITH EXTENDED ENDURANCE	BHATTACHARYYA, ARUP
<u>09944986</u>	6700771	150	08/30/2001	DECOUPLING CAPACITOR FOR	BHATTACHARYYA,

				HIGH FREQUENCY NOISE IMMUNITY	ARUP
<u>09984778</u>	<u>6933572</u>	150	10/31/2001	FIELD-SHIELDED SOI-MOS STRUCTURE FREE FROM FLOATING BODY EFFECT, AND METHOD OF FABRICATION THEREFOR	BHATTACHARYYA, ARUP
<u>10037081</u>	<u>6743681</u>	150	11/09/2001	METHODS OF FABRICATING GATE AND STORAGE DIELECTRIC STACKS HAVING SILICON-RICH-NITRIDE	BHATTACHARYYA, ARUP
<u>10075484</u>	<u>6784480</u>	150	02/12/2002	ASYMMETRIC BAND-GAP ENGINEERED NONVOLATILE MEMORY DEVICE	BHATTACHARYYA, ARUP
<u>10106915</u>	<u>7132348</u>	150	03/25/2002	LOW K INTERCONNECT DIELECTRIC USING SURFACE TRANSFORMATION	BHATTACHARYYA, ARUP
<u>10106916</u>	<u>6943065</u>	150	03/25/2002	SCALABLE HIGH PERFORMANCE ANTIFUSE STRUCTURE AND PROCESS	BHATTACHARYYA, ARUP
<u>10197978</u>	<u>6828632</u>	150	07/18/2002	STABLE PD-SOI DEVICES AND METHODS	BHATTACHARYYA, ARUP
<u>10198586</u>	<u>6903001</u>	150	07/18/2002	TECHNIQUES TO CREATE LOW K ILD FOR BEOL	BHATTACHARYYA, ARUP
<u>10232846</u>	<u>6917078</u>	150	08/30/2002	ONE TRANSISTOR SOI NON-VOLATILE RANDOM ACCESS MEMORY CELL	BHATTACHARYYA, ARUP
<u>10232848</u>	<u>6903969</u>	150	08/30/2002	ONE-DEVICE NON-VOLATILE RANDOM ACCESS MEMORY CELL	BHATTACHARYYA, ARUP
<u>10232855</u>	<u>7042027</u>	150	08/30/2002	GATED LATERAL THYRISTOR-BASED RANDOM ACCESS MEMORY CELL (GLTRAM)	BHATTACHARYYA, ARUP
<u>10243180</u>	<u>6759712</u>	150	09/12/2002	SEMICONDUCTOR-ON-INSULATOR THIN FILM TRANSISTOR CONSTRUCTIONS, AND METHODS OF MAKING SEMICONDUCTOR-ON-INSULATOR THIN FILM TRANSISTOR CONSTRUCTIONS	BHATTACHARYYA, ARUP
<u>10263608</u>	<u>6873015</u>	150	10/02/2002	SEMICONDUCTOR CONSTRUCTIONS COMPRISING THREE-DIMENSIONAL THIN FILM	BHATTACHARYYA, ARUP

				TRANSISTOR DEVICES AND RESISTORS	
<u>10264575</u>	<u>6998683</u>	150	10/03/2002	TFT-BASED COMMON GATE CMOS INVERTERS, AND COMPUTER SYSTEMS UTILIZING NOVEL CMOS INVERTERS	BHATTACHARYYA, ARUP
<u>10264914</u>	<u>6882010</u>	150	10/03/2002	HIGH PERFORMANCE THREE-DIMENSIONAL TFT-BASED CMOS INVERTERS, AND COMPUTER SYSTEMS UTILIZING SUCH NOVEL CMOS INVERTERS	BHATTACHARYYA, ARUP
<u>10364046</u>	<u>6768156</u>	150	02/10/2003	NON-VOLATILE RANDOM ACCESS MEMORY CELLS ASSOCIATED WITH THIN FILM CONSTRUCTIONS	BHATTACHARYYA, ARUP
<u>10364211</u>	<u>6800892</u>	150	02/10/2003	MEMORY DEVICES, AND ELECTRONIC SYSTEMS COMPRISING MEMORY DEVICES	BHATTACHARYYA, ARUP
<u>10364213</u>	<u>6812504</u>	150	02/10/2003	TFT-BASED RANDOM ACCESS MEMORY CELLS COMPRISING THYRISTORS	BHATTACHARYYA, ARUP
<u>10364271</u>	<u>7042052</u>	150	02/10/2003	TRANSISTOR CONSTRUCTIONS AND ELECTRONIC DEVICES	BHATTACHARYYA, ARUP
<u>10364710</u>	<u>6713810</u>	150	02/10/2003	NON-VOLATILE DEVICES, AND ELECTRONIC SYSTEMS COMPRISING NON-VOLATILE DEVICES	BHATTACHARYYA, ARUP
<u>10365947</u>	<u>7026690</u>	150	02/12/2003	MEMORY DEVICES AND ELECTRONIC SYSTEMS COMPRISING INTEGRATED BIPOLAR AND FET DEVICES	BHATTACHARYYA, ARUP
<u>10377904</u>	<u>6998667</u>	150	02/27/2003	SCALABLE GATE AND STORAGE DIELECTRIC	BHATTACHARYYA, ARUP
<u>10386619</u>	<u>6845034</u>	150	03/11/2003	ELECTRONIC SYSTEMS, CONSTRUCTIONS FOR DETECTING PROPERTIES OF OBJECTS, AND ASSEMBLIES FOR IDENTIFYING PERSONS	BHATTACHARYYA, ARUP
<u>10387090</u>	<u>6900667</u>	150	03/11/2003	LOGIC CONSTRUCTIONS AND ELECTRONIC DEVICES	BHATTACHARYYA, ARUP
<u>10425483</u>	<u>6888200</u>	150	04/29/2003	ONE TRANSISTOR SOI NON-VOLATILE RANDOM ACCESS	BHATTACHARYYA, ARUP

				MEMORY CELL	
<u>10454304</u>	Not Issued	93	06/03/2003	SRAM CONSTRUCTIONS, AND ELECTRONIC SYSTEMS COMPRISING SRAM CONSTRUCTIONS	BHATTACHARYYA, ARUP
<u>10612793</u>	Not Issued	41 <i>no DP / neg. res.</i>	07/02/2003	High-performance one-transistor memory cell	BHATTACHARYYA, ARUP
<u>10625068</u>	6908798	150	07/22/2003	METHODS OF MAKING SEMICONDUCTOR-ON- INSULATOR THIN FILM TRANSISTOR CONSTRUCTIONS	BHATTACHARYYA, ARUP
<u>10701696</u>	6873018	150	11/04/2003	MEMORY CELL CONSTRUCTIONS COMPRISING INTEGRATED BIPOLAR AND FET DEVICES	BHATTACHARYYA, ARUP
<u>10752351</u>	6955960	150	01/06/2004	DECOUPLING CAPACITOR FOR HIGH FREQUENCY NOISE IMMUNITY	BHATTACHARYYA, ARUP
<u>10759972</u>	6808971	150	01/14/2004	HIGH PERFORMANCE THREE- DIMENSIONAL TFT-BASED CMOS INVERTERS, AND COMPUTER SYSTEMS UTILIZING SUCH NOVEL CMOS INVERTERS	BHATTACHARYYA, ARUP
<u>10760087</u>	Not Issued	71	01/14/2004	High performance three- dimensional TFT-based CMOS inverters, and computer systems utilizing such novel CMOS inverters	BHATTACHARYYA, ARUP
<u>10781588</u>	6982457	150	02/17/2004	SEMICONDUCTOR DEVICES, AND ELECTRONIC SYSTEMS COMPRISING SEMICONDUCTOR DEVICES	BHATTACHARYYA, ARUP
<u>10788230</u>	7130216	150	02/26/2004	ONE-DEVICE NON-VOLATILE RANDOM ACCESS MEMORY CELL	BHATTACHARYYA, ARUP
<u>10840792</u>	Not Issued <i>no DP / neg. res.</i>	61	05/06/2004	Silicon on insulator read-write non- volatile memory comprising lateral thyristor and trapping layer	BHATTACHARYYA, ARUP
<u>10859543</u>	7019378	150	06/03/2004	FIELD-SHIELDED SOI-MOS STRUCTURE FREE FROM FLOATING BODY EFFECTS, AND METHOD OF FABRICATION THEREFOR	BHATTACHARYYA, ARUP
<u>10892340</u>	Not Issued <i>no DP</i>	94	07/14/2004	METHODS OF FORMING	BHATTACHARYYA,

	Issued			MEMORY DEVICES AND MEMORY CELL CONSTRUCTIONS	ARUP
10915618	6950340	150	08/10/2004	ASYMMETRIC BAND-GAP ENGINEERED NONVOLATILE MEMORY DEVICE	BHATTACHARYYA, ARUP
10925120	Not Issued <i>no DT (float.)</i>	95	08/24/2004	MEMORY CELL WITH TRENCHED GATED THYRISTOR	BHATTACHARYYA, ARUP

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